The influence of deposition temperature of *n*-type ALD buffer layer on device characteristics of electrodeposited Cu₂O thin film solar cells

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Beside several advantages, the PV power generation as a clean energy source, is still below the supply level due to high power generation cost. Therefore, the interest in fabricating low-cost thin film solar cells is increasing continuously. Cu_2O , a low cost photovoltaic material, has a wide direct band gap of ~2.1 eV has along with the high theoretical energy conversion efficiency of about 20%.[1,2] On the other hand, it has other benefits such as earth-abundance, low cost, non-toxic, high carrier mobility (100 cm²/Vs).[2,3] In spite of these various advantages, the efficiency of Cu_2O based solar cells is still significantly lower than the theoretical limit as reported in several literatures. One of the reasons behind the low efficiency of Cu_2O solar cells can be the formation of CuO layer due to atmospheric surface oxidation of Cu_2O absorber layer.[2,4]

In this work, atomic layer deposition method was used to remove the CuO layer that formed on Cu₂O surface. First, Cu₂O absorber layer was deposited by electrodeposition. On top of it buffer (ZnO) and TCO (AZO) layers were deposited by atomic layer deposition and rf-magnetron sputtering respectively. Figure 1 is SEM image of Cu₂O solar cell structure. We fabricated the cells with a change in the deposition temperature of buffer layer ranging between 80 °C to 140 °C. Finally, we compared the performance of fabricated solar cells, and studied the influence of buffer layer deposition temperature on Cu₂O based solar cells by J-V and XPS measurements.



Figure 1. SEM cross-sectional images of the Cu₂O solar cell

References:

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